

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~striketrough~~. When strikethrough cannot easily be perceived, or when five or fewer characters are deleted, [[double brackets]] are used to show the deletion. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered). Please CANCEL claims 4-6 and 18-21 without prejudice or disclaimer in accordance with the following:

1. (cancelled)
2. (cancelled)
3. (cancelled)
4. (cancelled)
5. (cancelled)
6. (cancelled)
7. (cancelled)
8. (cancelled)
9. (cancelled)
10. (cancelled)
11. (cancelled)
12. (cancelled)
13. (cancelled)
14. (previously presented) A semiconductor device, comprising:

a first insulating layer having vias extending therethrough;
a first conductive layer, comprising a first wiring pattern, embedded within the first insulating layer;
a second conductive layer, comprising a second wiring pattern, formed on the first insulating layer, the wiring pattern of the second conductive layer being electrically connected to the wiring pattern of the first conductive layer through the vias of the first insulating layer;
a semiconductor element embedded in the first insulating layer and electrically connected to the wiring pattern of the first conductive layer; and
a second insulating layer having a semiconductor element, electrically connected to the wiring pattern of the second conductive layer, embedded therein and embedding further therein the second conductive layer.

15. (cancelled)

16. (previously presented) The semiconductor device according to claim 14, wherein one or more of the wiring patterns of the first conductive layer is/are electrically connected to one or more of the wiring patterns of the second conductive layer through corresponding said vias.

17. (previously presented) A semiconductor device, comprising:
a substrate;
a first set of conductors comprising a first conductive layer formed on the substrate;
a first insulating layer formed on the first set of conductors and having vias extending therethrough, the first insulating layer having at least one semiconductor element and the first set of conductors embedded therein;
a second set of conductors comprising a second conductive layer formed on the first insulating layer and extending through vias therein; and
a second insulating layer formed on the second set of conductors and having vias extending therethrough, the second insulating layer having at least one semiconductor element and portions of the second set of conductors embedded therein;
wherein one or more of the first set of conductors is/are electrically connected to the at least one semiconductor element embedded in the first insulating layer and one or more of the second set of conductors is/are electrically connected to the at least one semiconductor element embedded in the second insulating layer and through corresponding said vias to one or more of the first set of conductors.

18. (cancelled)

19. (cancelled)

20. (cancelled)

21. (cancelled)